

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	4	(expos\$3) near15 (aluminum near3 gas) near25 (silicon near gas)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:50	
2	BRS	L2	2637	(expos\$3) near15 (aluminum or al) near25 (silicon or si)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:50	
3	BRS	L3	2934	(expos\$3) near15 (((aluminum or al)) near25 ((silicon or si)))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:51	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	11	(expos\$3) near15 (((aluminum or al))) near25 ((silicon or si))) near20 (saturat\$2)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:52	
5	BRS	L5	12	(expos\$3 or radiat\$3) near15 (((aluminum or al))) near25 ((silicon or si))) near20 (saturat\$2)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:52	
6	BRS	L6	12	((expos\$3 or radiat\$3 or irradiat\$3)) near15 (((aluminum or al))) near25 ((silicon or si))) near20 (saturat\$2)	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:53	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	12	((expos\$3 or radiat\$3 or irradiat\$3)) near15 (((aluminum or al)) near25 ((silicon or si))) near20 ((saturat\$2))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:54	
8	BRS	L8	4987	((expos\$3 or radiat\$3 or irradiat\$3)) near15 (((aluminum or al)) near25 ((silicon or si)))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:55	
9	BRS	L9	1670	((expos\$3 or radiat\$3 or irradiat\$3)) near15 (((aluminum or al)) near25 ((silicon or si))) near25 ((substrate or device or semiconductor))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:56	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	284	((expos\$3 or radiat\$3 or irradiat\$3)) near15 (((aluminum or al)) near25 ((silicon or si))) near25 ((substrate or device or semiconductor)) near25 ((dielectric or insulat\$3))	US- PGPU B; USPA T; EPO; JPO; DERW ENT; IBM_ TDB	2004/11/ 16 11:57	

	U	1	PT	P	Document ID	Issue Date	Page s	Title
1					US 6210991 B1	20010403	11	Metal contact scheme using selective silicon growth
2					US 6136212 A	20001024	17	Polymer-based micromachining for microfluidic devices
3					US 4610936 A	19860909	11	Hot-dip zinc alloy coated steel products
4					US 4113548 A	19780912	5	Process for the production of silicon layers

	U	1	PT	P	Document ID	Issue Date	Page s	Title
5					US 4040869 A	19770809	9	High voltage deep diode power semiconductor switch
6					US 4040171 A	19770809	10	Deep diode zeners

	U	1	PT	P	Document ID	Issue Date	Page s	Title
7					US 3988769 A	19761026	6	High voltage diodes
8					US 3988757 A	19761026	10	Deep diode zeners

	U	1	PT	P	Document ID	Issue Date	Page s	Title
9					US 3982269 A	19760921	11	Semiconductor devices and method, including TGZM, of making same
10					US 3975213 A	19760817	6	High voltage diodes
11					JP 01110749 A	19890427	3	MANUFACTURE OF SEMICONDUCTOR DEVICE

	U	1	PT	P	Document ID	Issue Date	Page s	Title
12	X				JP 10144615 A	19980529	6	SOI wafer manufacture employing liquid phase growth technique for semiconductor IC - involves precipitate saturated silicon solution applied onto silicon made film surface by cooling so as to form silicon film on it